

**REMARKS**

Claims 60-62 and 66 are amended. Claims 63, 67-68 and 70 are cancelled. Claims 60-62, 64 and 66 are pending in the application.

Claims 60-64, 66-68 and 70 stand rejected under 35 U.S.C. § 112, first paragraph, as failing to comply with the written description requirement. The Examiner indicates that the recited “without feeding added ozone into the chemical vapor deposition reactor” is not sufficiently supported by the specification. The Examiner additionally indicates that the limitation “to directly deposit SiO<sub>2</sub>” is not sufficiently supported by the specification. Applicant disagrees with the Examiner’s position for reasons of record. However, in order to expedite prosecution of the application, independent claim 60 is amended to no longer recite the limitation “without feeding added ozone” or direct deposition of SiO<sub>2</sub>. Accordingly, applicant respectfully requests withdrawal of the § 112 rejection of claim 60 and the claims that depend therefrom in the Examiner’s next action.

Claims 60-64 and 66-68 stand rejected under 35 U.S.C. § 102(b) as being anticipated by Morita, U.S. Patent No. 5,360,646; and as being unpatentable over Sukharev, U.S. Patent No. 5,710,079. In accordance with MPEP § 2131, anticipation requires each and every element of a claim to be disclosed in a single prior art reference. Pending claims 60-62, 64 and 66 are allowable over Sukharev and Morita for at least the reason that neither of the references discloses each and every element in any of those claims.

As amended, independent claim 60 recites a method of depositing SiO<sub>2</sub> by providing a substrate within a cold-wall CVD reactor, providing rf power of 600W and a temperature of 400°C and injecting liquid TEOS at 975 sccm. Claim 60 further recites feeding gaseous

H<sub>2</sub>O<sub>2</sub> into the reactor and decomposing the TEOS to form SiO<sub>2</sub> and depositing the SiO<sub>2</sub> onto the substrate, where the decomposition is conducted at a pressure of 10 Torr to about 80 Torr. The amendment to claim 60 is supported by the specification at, for example, page 11, lines 9-20. Neither Sukharev nor Morita discloses the claim 60 recited injecting liquid TEOS into a cold-wall CVD reactor under the recited conditions. Applicant notes that the Examiner relies upon Wolf, et al. "Silicon Processing for the VLSI Era", Vol. 1 pp. 166-167, for providing a definition of a cold-wall reactor. Such reference does not disclose the claim 60 recited injecting liquid TEOS into a cold-wall reactor under the recited conditions. Accordingly, claim 60 is not anticipated by any of the cited references and is therefore allowable.

Claims 63 and 67-68 are cancelled. Claims 61, 62 and 66 are amended to properly depend from independent claim 61. Dependent claims 61, 62, 64 and 66 are allowable over Sukharev, Morita and Wolf for at least the reason that they depend from allowable base claim 60.

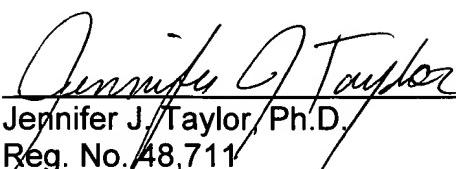
Claim 70 stands rejected under 35 U.S.C. § 103(a) as being unpatentable over a combination of Morita and Cummings, U.S. Patent No. 4,843,867; and as being unpatentable over Sukharev. Without admission as to the propriety of the Examiner's rejection of claim 70, such claim is cancelled.

For the reasons discussed above, pending claims 60-62, 64 and 66 are allowable. Accordingly, applicant respectfully requests formal allowance of such pending claims in the Examiner's next action.

Respectfully submitted,

Dated: December 27, 2004

By:

  
\_\_\_\_\_  
Jennifer J. Taylor, Ph.D.  
Reg. No. 48,711